

1 1. A method comprising:
2 providing localized heating to a lithography mask
3 to adjust for optical limitations in the mask formation
4 process.

1 2. The method of claim 1 wherein providing localized
2 heating to adjust for the proximity effect.

1 3. The method of claim 1 including providing
2 localized heating to adjust for line end shortening.

1 4. The method of claim 1 wherein providing localized
2 heating includes directing a laser beam to a localized
3 region.

1 5. The method of claim 1 wherein providing localized
2 heating includes forming a silicide between a silicon
3 containing layer and another layer.

1 6. The method of claim 1 including providing
2 localized heating to an extreme ultraviolet lithography
3 mask.

1 7. A lithography mask comprising:
2 a substrate; and
3 a stack over said substrate, said stack being
4 thermally modified in a localized region.

1 8. The mask of claim 7 wherein said mask is an
2 extreme ultraviolet lithography mask.

1 9. The mask of claim 7 wherein said mask is modified
2 in a localized region to correct line end shortening.

1 10. The mask of claim 7 wherein said mask is modified
2 in a localized region to reduce the proximity effect.

1 11. The mask of claim 7 wherein said mask includes a
2 silicide in a localized region.

1 12. The mask of claim 7 wherein said stack includes
2 layers of silicon and another material.

1 13. The mask of claim 12 wherein said silicon is
2 converted to silicide in a localized region.

1 14. An ultraviolet lithography mask comprising:
2 a substrate; and
3 a stack over said substrate, said stack including
4 alternating layers of silicon and another material, and
5 localized regions of silicide formed in a silicon layer.

1 15. The mask of claim 14 wherein said mask is
2 modified in a localized region to correct line end
3 shortening.

1 16. The mask of claim 14 wherein said mask is
2 modified in a localized region to reduce the proximity
3 effect.